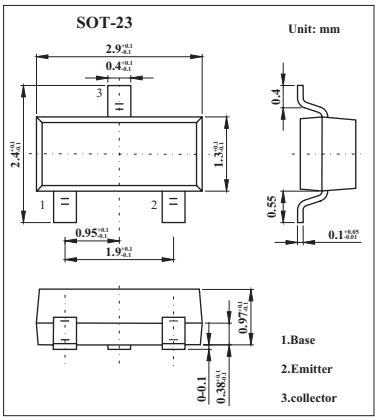
Silicon PNP Epitaxial

2SA1122



■ Features

● Low frequency amplifier

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-55	V
Collector to emitter voltage	V_{CEO}	-55	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 μA, I_E = 0	-55			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1 mA, R_{BE} = ∞	-55			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 μA, I_C = 0	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -30 V, I_E = 0			-0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB} = -2 V, I_C = 0			-0.5	μA
DC current transfer ratio	h_{FE}	V_{CE} = -12 V, I_C = -2 mA	160		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = -10 mA, I_B = -1 mA			-0.5	V
Base to emitter voltage	V_{BE}	V_{CE} = -12 V, I_C = -2 mA			-0.75	V

■ h_{FE} Classification

Marking	CC	CD	CE
hFE	160～320	250～500	400～800